

IN THE CLAIMS

1-24 (Canceled).

25. (Currently Amended) A semiconductor circuit on a semiconductor chip comprising:

a first access port and a second access port; and  
a plurality of memory banks which can be accessed through both said first access port and said second access port; and

an access priority judgment unit;

wherein each of said plurality of memory banks ~~each~~ includes a plurality of word lines, a plurality of bit lines, a plurality of memory DRAM-cells, and a sense amplifier circuit, ~~and~~

wherein said access priority judgment unit gives priority to one of said first and second access ports ~~has priority over~~ the other of said first and second access ports when said first and second access ports access a same memory bank of said plurality of memory banks, and

wherein said access priority judgment unit allows parallel access to said first and second access ports when said first and second access ports access different memory banks respectively.

26. (Previously Presented) The semiconductor circuit according to claim 25,

wherein said plurality of memory banks each further includes global bit lines coupled to said plurality of bit pairs.

27. (Previously Presented) The semiconductor circuit according to claim 26, further comprising:

a decision circuit which sets said priority among said access ports.

28. (Currently Amended) ~~The semiconductor circuit according to claim 27,~~ A semiconductor circuit on a semiconductor chip comprising:

a first access port and a second access port;

a plurality of memory banks which can be accessed through both said first access port and said second access port; and

a decision circuit which sets said priority among said access ports;

wherein each of said plurality of memory banks includes a plurality of word lines, a plurality of bit lines, a plurality of DRAM cells, and a sense amplifier circuit,

wherein one of said first and second access ports has priority over the other of said first and second access ports when said first and second access ports access a same memory bank of said plurality of memory banks, and

wherein said first and second access ports handle different bit widths.

29. (Currently Amended) The semiconductor circuit according to claim ~~27~~ 28, further comprising:

a hit/miss judgment circuit,

~~wherein said first access port and said second access port handle different bit widths~~

wherein said hit/miss judgment circuit judges hit/miss based on access request, and outputs data which is already latched by said sense amplifier to said global bit lines in case of hit.

30. (Previously Presented) The semiconductor circuit according to claim 29,

wherein an access to one of said plurality of memory banks through said first access port and an access to another one of said plurality of memory banks through said second access port has an overlapping period.

31. (Previously Presented) A semiconductor circuit on a semiconductor chip comprising:

a first access port and a second access port;

a plurality of memory banks which can be accessed through said first access port and said second access port;

wherein said plurality of memory banks each includes a plurality of word lines, a plurality of bit lines, a plurality of memory DRAM cells, and a sense amplifier circuit,

wherein one of said first and second access ports has priority over the other of said first and second access ports when there is a conflict between accesses from said first access port and said second access port, and

wherein when an access through said first access port is a miss and an access through said second access port is a hit, data is outputted through said second access port until an output through said first access port is ready.

32. (Previously Presented) The semiconductor circuit according to claim 31,

wherein said plurality of memory banks each further includes global bit lines coupled to said plurality of bit pairs.

33. (Currently Amended) The semiconductor circuit according to claim 32, further comprising:

a hit/miss judgment circuit,

wherein said first access port and said second access port handle different bit widths, and

wherein said hit/miss judgment circuit judges  
hit/miss based on access request, and outputs data which is  
already latched by said sense amplifier to said global bit  
lines in case of hit.

34. (Previously Presented) The semiconductor circuit  
according to claim 33,

          wherein an access to one of said plurality of memory  
banks through said first access port and an access to another  
one of said plurality of memory banks through said second  
access port has an overlapping period.